

5SNA 1000G650300

HiPak IGBT module



- $V_{CE} = 6500\text{ V}$
- $I_C = 1000\text{ A}$
- Ultra-low-loss, rugged SPT++ chip-set
- Exceptional ruggedness and highest current rating
- High insulation package
- AlSiC base-plate and AlN substrate for low thermal resistance and high power cycling capability
- Recognized under UL1557, File E196689

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	V_{CES}	$V_{GE} = 0\text{ V}$, $T_{vj} \geq 25\text{ °C}$		6500	V
DC collector current	I_C	$T_C = 110\text{ °C}$, $T_{vj} = 150\text{ °C}$		1000	A
Peak collector current	I_{CM}	$t_p = 1\text{ ms}$		2000	A
Gate-emitter voltage	V_{GES}		-20	20	V
DC forward current	I_F			1000	A
Peak forward current	I_{FRM}	$t_p = 1\text{ ms}$		2000	A
Surge current	I_{FSM}	$V_R = 0\text{ V}$, $T_{vj} = 150\text{ °C}$, $t_p = 10\text{ ms}$, half-sinewave		11000	A
IGBT short circuit SOA	t_{psc}	$V_{CC} = 4500\text{ V}$, $V_{CEM\text{ CHIP}} \leq 6500\text{ V}$ $V_{GE} \leq 15\text{ V}$, $T_{vj} \leq 150\text{ °C}$		10	μs
Isolation voltage	V_{isol}	1 min, $f = 50\text{ Hz}$		10200	V
Junction temperature	T_{vj}			175	$^{\circ}\text{C}$
Junction operating temperature	$T_{vj(op)}$		-40	150	$^{\circ}\text{C}$
Case temperature	T_C		-50	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-50	125	$^{\circ}\text{C}$
Mounting torques	M_s	Base-heatsink, M6 screws	4	6	Nm
	M_{t1}	Main terminals, M8 screws	8	10	
	M_{t1}	Auxiliary terminals, M4 screws	2	3	

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

IGBT characteristic values ²⁾

Parameter	Symbol	Conditions	min	typ.	max	Unit	
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}, I_C = 10 \text{ mA}$	$T_{vj} = 150 \text{ }^\circ\text{C}$	6500		V	
			$T_{vj} = 25 \text{ }^\circ\text{C}$	6500		V	
			$T_{vj} = -40 \text{ }^\circ\text{C}$	6000		V	
Collector-emitter ³⁾ saturation voltage	$V_{CE\text{sat}}$	$I_C = 1000 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		3.1	3.6	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		4.1	4.7	V
			$T_{vj} = 150 \text{ }^\circ\text{C}$		4.4		V
Collector cut-off current	I_{CES}	$V_{CE} = 6500 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$			1	mA
			$T_{vj} = 125 \text{ }^\circ\text{C}$		25	70	mA
			$T_{vj} = 150 \text{ }^\circ\text{C}$		95		mA
Gate leakage current	I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$	-500		500	nA	
Gate-emitter threshold voltage	$V_{GE(TO)}$	$I_C = 240 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25 \text{ }^\circ\text{C}$	5.5		7.5	V	
Gate charge	Q_{ge}	$I_C = 1000 \text{ A}, V_{CE} = 3600 \text{ V}, V_{GE} = -15 \text{ V} \dots +15 \text{ V}$		8.3		μC	
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}, V_{GE} = 0 \text{ V}, f = 1 \text{ MHz}, T_{vj} = 25 \text{ }^\circ\text{C}$		101		nF	
Internal gate resistance	R_{Gint}			0.74			
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 1.5 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		520		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$		500		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$		500		ns
Rise time	t_r	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 1.5 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		155		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$		160		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$		160		ns
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 15 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		5000		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$		5650		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$		5900		ns
Fall time	t_f	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 15 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		380		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$		460		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$		500		ns
Turn-on switching energy	E_{on}	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 1.5 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		4100		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		5250		mJ
			$T_{vj} = 150 \text{ }^\circ\text{C}$		5800		mJ
Turn-off switching energy	E_{off}	$V_{CC} = 3600 \text{ V}, I_C = 1000 \text{ A}, R_G = 15 \text{ } \Omega, C_{GE} = 220 \text{ nF}, V_{GE} = \pm 15 \text{ V}, L_\sigma = 150 \text{ nH}, \text{ inductive load}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		4200		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		5400		mJ
			$T_{vj} = 150 \text{ }^\circ\text{C}$		5650		mJ
Short circuit current	I_{SC}	$t_{psc} \leq 10 \text{ } \mu\text{s}, V_{GE} = 15 \text{ V}, V_{CC} = 4500 \text{ V}, V_{CEM\text{CHIP}} \leq 6500 \text{ V}$	$T_{vj} = 150 \text{ }^\circ\text{C}$	4800		A	

²⁾ Characteristic values according to IEC 60747 – 9³⁾ Collector-emitter saturation voltage is given at chip level

Diode characteristic values ⁴⁾

Parameter	Symbol	Conditions	min	typ.	max	Unit	
Forward voltage ⁵⁾	V_F	$I_F = 1000 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	3.05	3.5	V	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		3.4	3.9	V
			$T_{vj} = 150 \text{ }^\circ\text{C}$		3.35		V
Reverse recovery current	I_{rr}		$T_{vj} = 25 \text{ }^\circ\text{C}$	1710		A	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2230		A
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2490		A
Recovered charge	Q_{rr}	$V_{CC} = 3600 \text{ V},$ $I_F = 1000 \text{ A},$ $V_{GE} = \pm 15 \text{ V},$ $R_G = 1.5 \text{ } \Omega,$ $C_{GE} = 220 \text{ nF},$ $L_\sigma = 150 \text{ nH}$ inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	1210		μC	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1950		μC
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2260		μC
Reverse recovery time	t_{rr}		$T_{vj} = 25 \text{ }^\circ\text{C}$	1400		ns	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1400		ns
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1380		ns
Reverse recovery energy	E_{rec}		$T_{vj} = 25 \text{ }^\circ\text{C}$	2300		mJ	
			$T_{vj} = 125 \text{ }^\circ\text{C}$		4150		mJ
			$T_{vj} = 150 \text{ }^\circ\text{C}$		4900		mJ

⁴⁾ Characteristic values according to IEC 60747 – 2⁵⁾ Forward voltage is given at chip levelPackage properties ⁶⁾

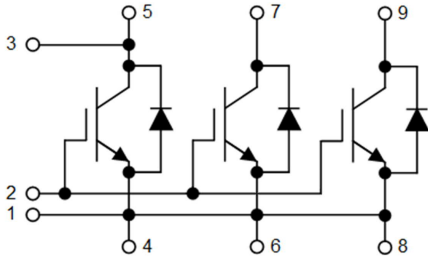
Parameter	Symbol	Conditions	min	typ.	max	Unit	
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$				0.0098	K/W	
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$				0.016	K/W	
IGBT thermal resistance ²⁾ case to heatsink	$R_{th(c-s)IGBT}$	IGBT per switch, λ grease = $1\text{W/m} \times \text{K}$		0.008		K/W	
Diode thermal resistance ²⁾ case to heatsink	$R_{th(c-s)DIODE}$	Diode per switch, λ grease = $1\text{W/m} \times \text{K}$		0.011		K/W	
Partial discharge voltage	V_e	$f = 50 \text{ Hz}, Q_{PD} \leq 10\text{pC}$ (acc. to IEC 61287)	5100			V	
Comparative tracking index	CTI		600			V	
Module stray inductance	$L_{\sigma CE}$			18		nH	
Resistance, terminal-chip	$R_{CC+EE'}$		$T_C = 25 \text{ }^\circ\text{C}$	0.07		m Ω	
			$T_C = 125 \text{ }^\circ\text{C}$		0.1		m Ω
			$T_C = 150 \text{ }^\circ\text{C}$		0.11		m Ω

Mechanical properties ⁶⁾

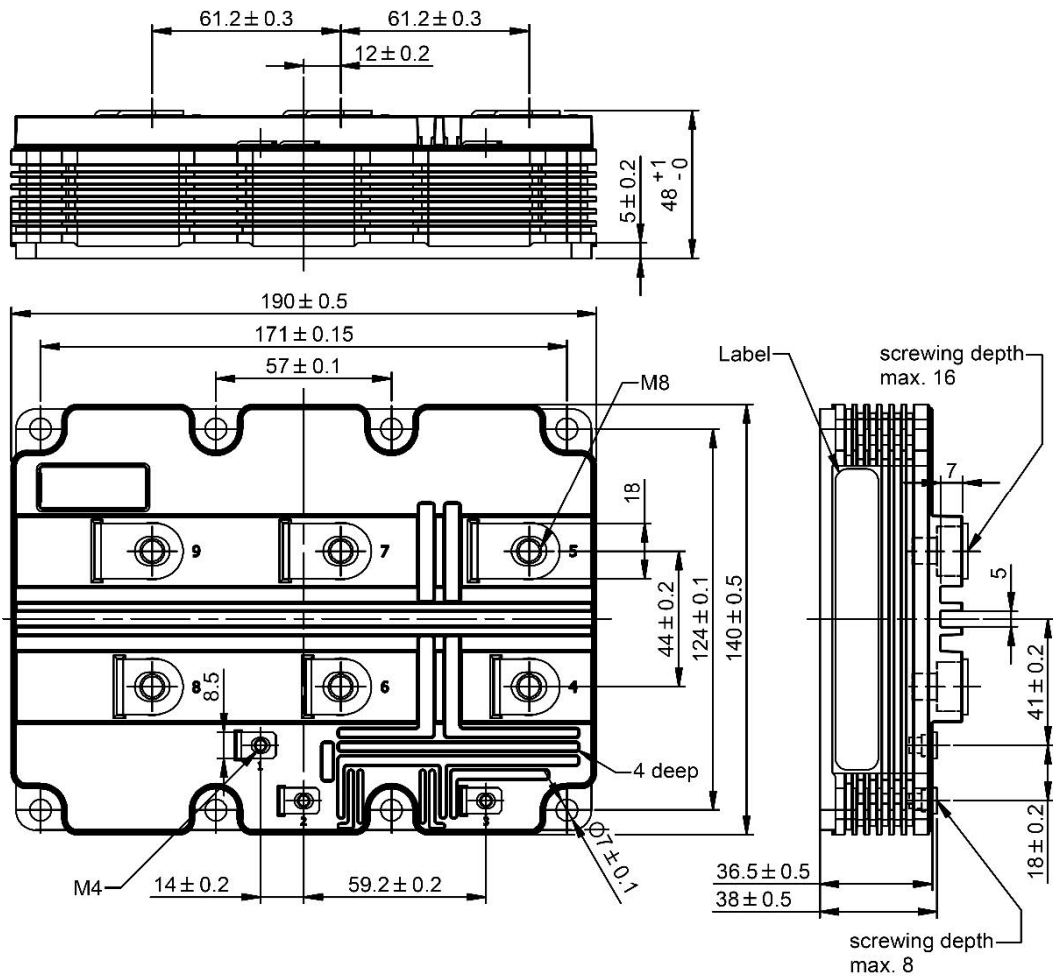
Parameter	Symbol	Conditions	min	typ.	max	Unit
Dimensions	L x W x H	Typical		190 x 140 x 48		mm
Clearance distance in air	d_a	According to IEC 60664-1 and EN 50124-1	Term. to base:	40		mm
			Term. to term:	26		mm
Surface creepage distance	d_s	According to IEC 60664-1 and EN 50124-1	Term. to base:	64		mm
			Term. to term:	56		mm
Mass	m			1330		g

⁶⁾ Package and mechanical properties according to IEC 60747 – 15

Electrical configuration



Outline drawing (mm)



Note: This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chapter VIII. This product has been designed and qualified for industrial level.

Fig. 1 Typical on-state characteristics, chip level

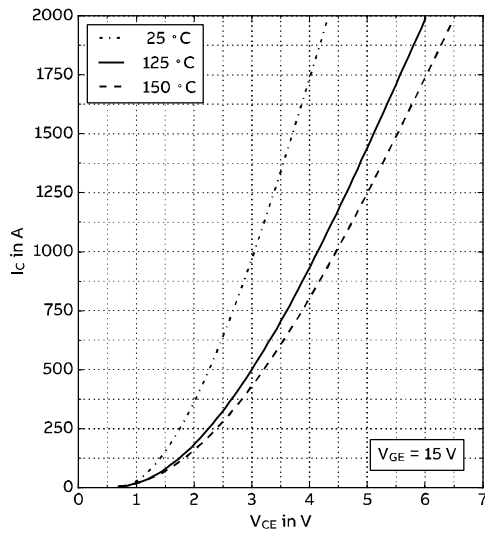


Fig. 2 Typical transfer characteristics, chip level

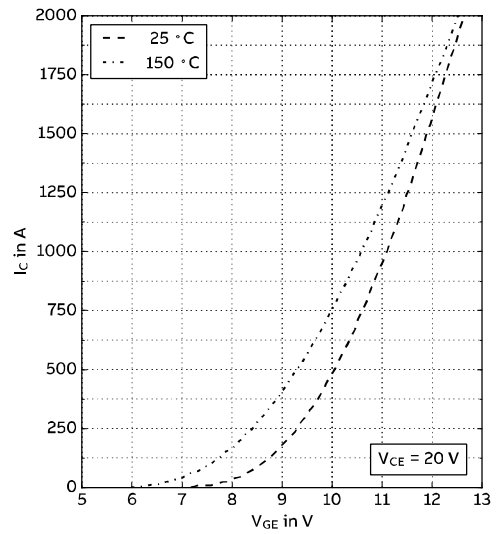


Fig. 3 Typical output characteristics, chip level

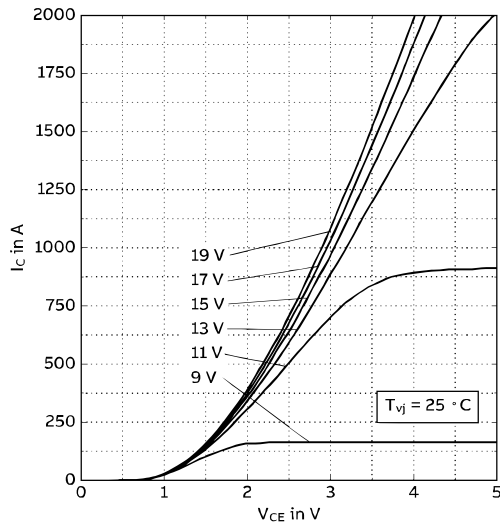


Fig. 4 Typical output characteristics, chip level

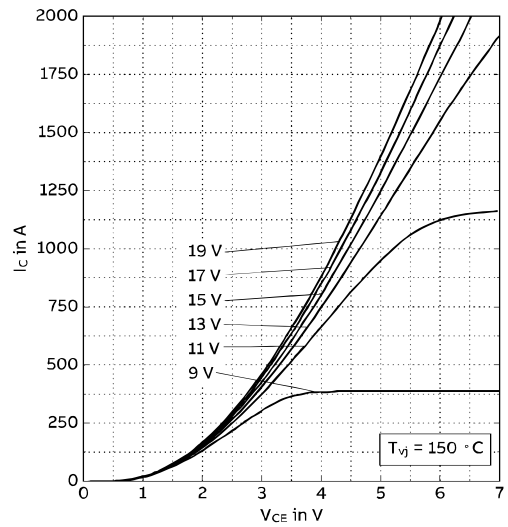


Fig. 5 Typical switching energies per pulse vs. collector current

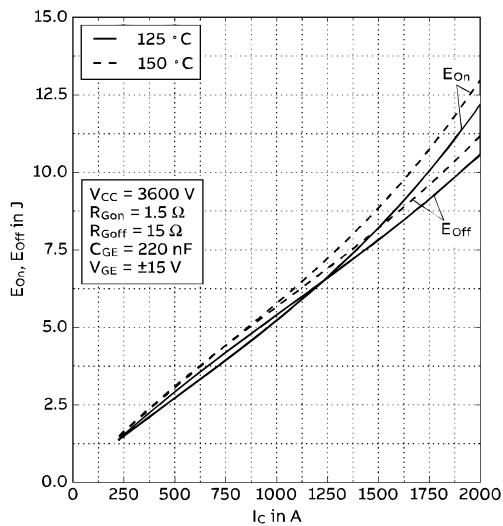


Fig. 6 Typical switching energies per pulse vs. gate resistor

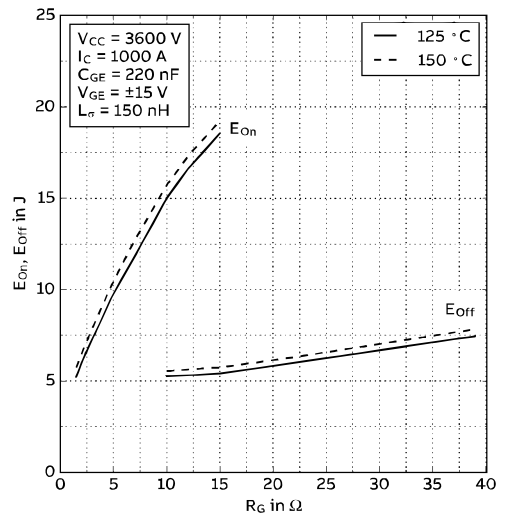


Fig. 7 Typical switching times vs. collector current

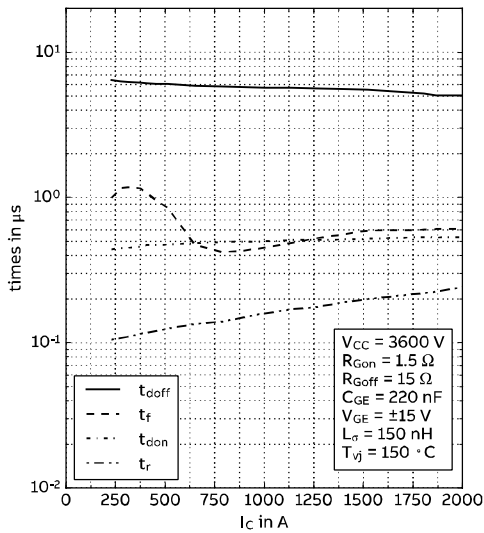


Fig. 8 Typical switching times vs. gate resistor

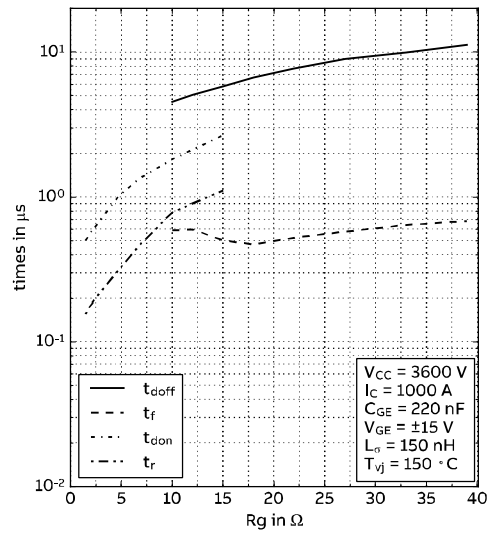


Fig. 9 Typical gate charge characteristics

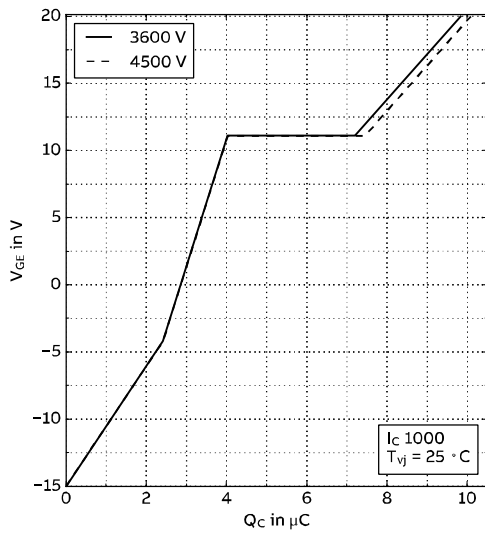


Fig. 10 Turn-off safe operating area (RBSOA)

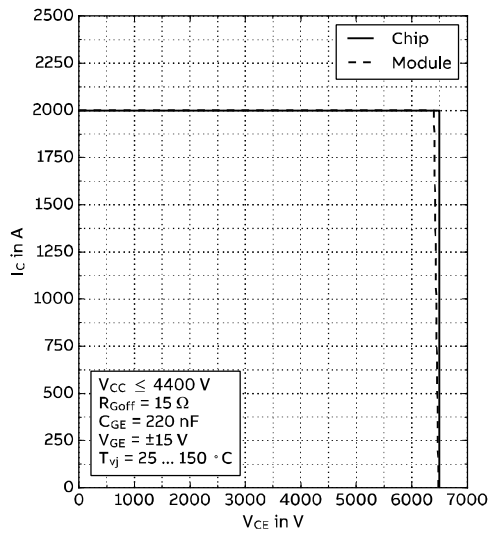


Fig. 11 Typical diode forward characteristics chip level

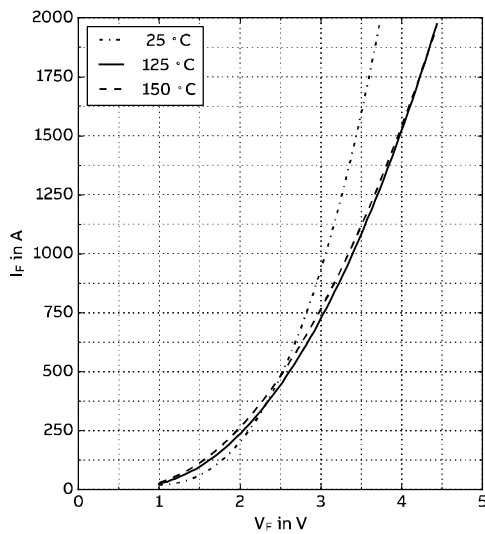


Fig. 12 Typical reverse recovery characteristics vs. forward current

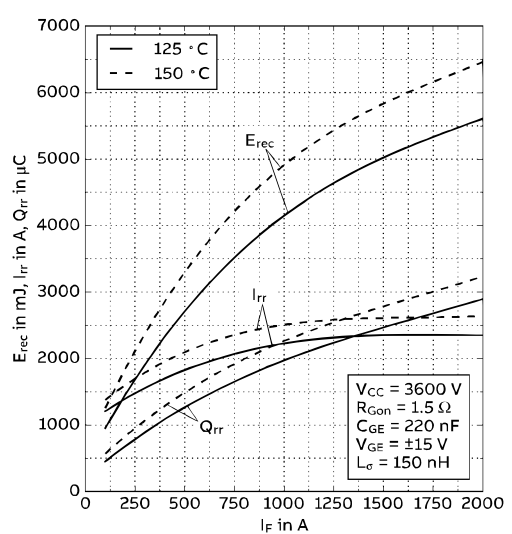


Fig. 13 Typical reverse recovery characteristics vs. di/dt

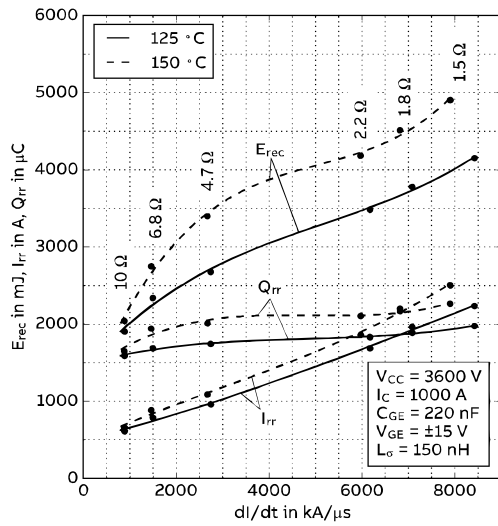


Fig. 14 Safe operating area diode (SOA)

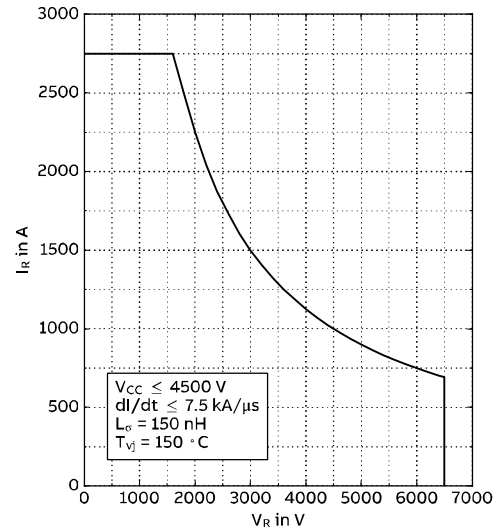
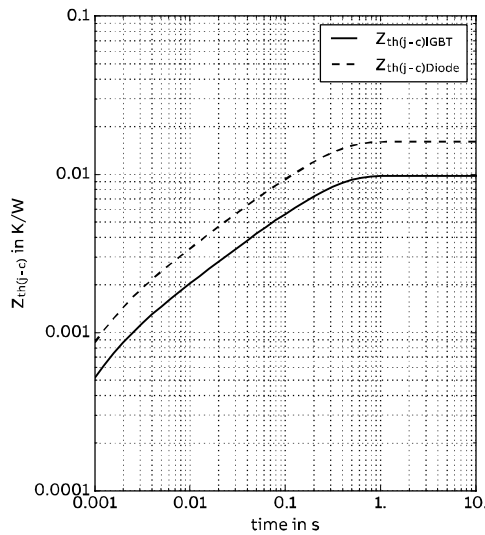


Fig. 15 Thermal impedance vs. time



Analytical function of the transient thermal resistance

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

	i	1	2	3	4	5
IGBT	R _i (K/kW)	0.9	2.35	4.84	1.68	
	τ _i (ms)	3609	364	51	3.7	
DIODE	R _i (K/kW)	1.95	6.11	5.9	2.06	
	τ _i (ms)	2283	160	32	2.7	

Related documents:

- 5SYA 2039 Mounting Instructions for HiPak modules
- 5SYA 2042 Failure rates of IGBT modules due to cosmic rays
- 5SYA 2043 Load – cycle capability of HiPaks
- 5SYA 2045 Thermal runaway during blocking
- 5SYA 2053 Applying IGBT
- 5SYA 2058 Surge currents for IGBT diodes
- 5SYA 2093 Thermal design of IGBT modules
- 5SYA 2098 Paralleling of IGBT modules
- 5SZK 9111 Specification of environmental class for HiPak Storage
- 5SZK 9112 Specification of environmental class for HiPak Transportation
- 5SZK 9113 Specification of environmental class for HiPak Operation (Industry)
- 5SZK 9120 Specification of environmental class for HiPak

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